

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	10/721870	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/02 16:45
S2	8	("6313010") or ("6180493") or ("6258695") or ("5874368").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 11:13
S3	1	10/721080	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 06:56
S4	21053	isolation near trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 09:58
S5	392	S4 and liner near3 silicon near nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 09:58
S6	248	S5 and silicon adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 09:59
S7	14	S6 and (silicon adj oxide) near3 bur\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 09:59
S8	2300	(257/506-510).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 09:57
S9	5403	(438/207,218,219,294,427,221,296, 353,424,221,700).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 09:58
S10	21114	isolation near trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 07:14

S11	12913	S10 and "257"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 06:57
S12	300	S11 and liner near3 silicon near nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 07:14
S13	200	S12 and silicon adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 07:14
S14	50	S13 and void	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 07:14
S15	7	S14 and (silicon adj oxide) near3 bur\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 07:25
S16	1	S15 and active near region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 07:08
S17	308960	(isolation near trench) TI	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 10:49
S18	434	S17 and liner near3 silicon near nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 10:50
S19	271	S18 and silicon adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 10:51
S20	70	S19 and void	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 12:13

S21	11	S20 and (silicon adj oxide) near3 bur\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 10:51
S22	4	S21 not S15	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 07:16
S23	1	((silicon adj oxide) near3 bur\$3) and (void with silicon adj nitride). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 07:29
S24	312270	(isolation near trench) TI STI	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 12:12
S25	440	S24 and liner near3 silicon near nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 12:12
S26	276	S25 and silicon adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 12:12
S27	14	S26 and (silicon adj oxide) near3 bur\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 10:51
S28	11	S27 and void	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 10:53
S29	7	S28 not S22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 10:54
S30	3	S27 not S21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 10:54

S31	2408	(257/506-510).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 09:58
S32	5722	(438/207,218,219,294,427,221,296, 353,424,221,700).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 09:58
S33	23420	isolation near trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 09:58
S34	446	S33 and liner near3 silicon near nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 10:07
S35	16	S34 and (silicon adj oxide) near3 bur\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 10:00
S36	282	S34 and silicon adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 09:59
S37	16	S36 and (silicon adj oxide) near3 bur\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 10:01
S38	767	S31 and S33	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 10:01
S39	2259	S32 and S33	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 10:01
S40	5722	(438/207,218,219,294,427,221,296, 353,424,221,700).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 10:07

S41	23420	isolation near trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 10:07
S42	2259	S40 and S41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 10:07
S43	135	S42 and liner near3 silicon near nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 10:09
S44	325828	(isolation near trench) TI STI	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 12:12
S45	499	S44 and liner near3 silicon near nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 12:12
S46	314	S45 and silicon adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 12:12
S47	83	S46 and void	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 12:13
S49	1	(silicon adj nitride and lower adj inner and retract\$3 near5 (surface near3 substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 13:41
S50	1	(silicon adj nitride and lower adj inner and retract\$3 with (surface near3 substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 13:41

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L1	1	(silicon adj nitride and lower adj inner and retract\$3 near5 (surface near3 substrate)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 13:46